



STD3LN62K3, STF3LN62K3 STP3LN62K3, STU3LN62K3

N-channel 620 V, 2.5 Ω , 2.5 A SuperMESH3™ Power MOSFET
DPAK, TO-220FP, TO-220, IPAK

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D	P _D
STD3LN62K3	620 V	< 3 Ω	2.5 A	45 W
STF3LN62K3			2.5 A ⁽¹⁾	20 W
STP3LN62K3			2.5 A	45 W
STU3LN62K3			2.5 A	45 W

1. Limited by package

- 100% avalanche tested
- Extremely high dv/dt capability
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Application

Switching applications

Description

These devices are made using the SuperMESH3™ Power MOSFET technology that is obtained via improvements applied to STMicroelectronics' SuperMESH™ technology combined with a new optimized vertical structure. The resulting product has an extremely low on resistance, superior dynamic performance and high avalanche capability, making it especially suitable for the most demanding applications.

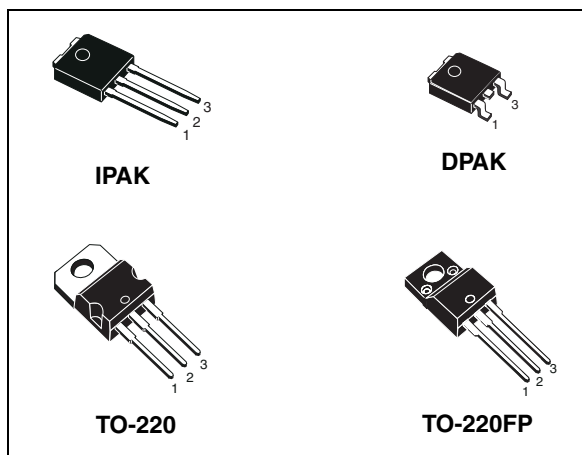


Figure 1. Internal schematic diagram

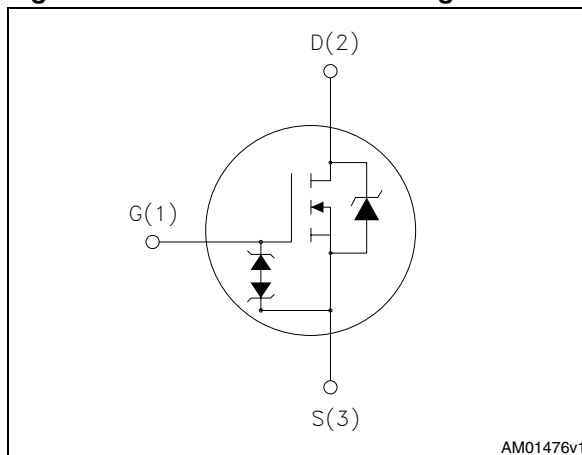


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD3LN62K3	3LN62K3	DPAK	Tape and reel
STF3LN62K3		TO-220FP	Tube
STP3LN62K3		TO-220	
STU3LN62K3		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220	PAK IPAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	620			V
V_{GS}	Gate- source voltage	± 30			V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	2.5		2.5 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	1.6		1.6 ⁽¹⁾	A
I_{DM} ⁽²⁾	Drain current (pulsed)	10		10 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	45		20	W
	Derating factor	0.36		0.16	W/ $^{\circ}\text{C}$
$V_{ESD(G-S)}$	Gate source ESD (HBM-C = 100 pF, R = 1.5 k Ω)	2500			V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	12			V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25\text{ }^{\circ}\text{C}$)	2500			V
T_{stg}	Storage temperature	-55 to 150			$^{\circ}\text{C}$
T_j	Max. operating junction temperature	150			$^{\circ}\text{C}$

1. Limited by package

2. Pulse width limited by safe operating area

3. $I_{SD} \leq 2.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, peak $V_{DS} < V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$
Table 3. Thermal data

Symbol	Parameter	TO-220	PAK IPAK	TO-220FP	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.78		6.25	$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max		50		$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb max	62.5	100	62.5	$^{\circ}\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300		300	$^{\circ}\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	2.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	90	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	620			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.25\text{ A}$		2.5	3	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	386	-	pF
C_{oss}	Output capacitance			30		pF
C_{rss}	Reverse transfer capacitance			5		pF
$C_{o(tr)}^{(1)}$	Eq. capacitance time related	$V_{GS} = 0$, $V_{DS} = 0\text{ to }496\text{ V}$	-	20	-	pF
$C_{o(er)}^{(2)}$	Eq. capacitance energy related		-	28	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	7	-	Ω
Q_g	Total gate charge	$V_{DD} = 496\text{ V}$, $I_D = 2.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 20)	-	17	-	nC
Q_{gs}	Gate-source charge			2.7		nC
Q_{gd}	Gate-drain charge			10.7		nC

1. $C_{oss\text{ eq.}}$ time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

2. $C_{oss\text{ eq.}}$ energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 310\text{ V}$, $I_D = 1.25\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 19)	-	9	-	ns
t_r	Rise time			7		ns
$t_{d(off)}$	Turn-off-delay time			30		ns
t_f	Fall time			27		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				10	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.5\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 24)	-	240		ns
Q_{rr}	Reverse recovery charge			1200		nC
I_{RRM}	Reverse recovery current			10		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 24)	-	265		ns
Q_{rr}	Reverse recovery charge			1400		nC
I_{RRM}	Reverse recovery current			11		A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{gs} = \pm 1\text{ mA}$ (open drain)	30	-		V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

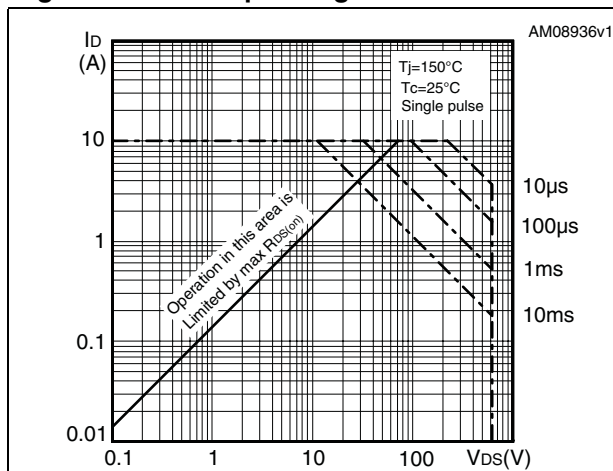


Figure 3. Thermal impedance for TO-220

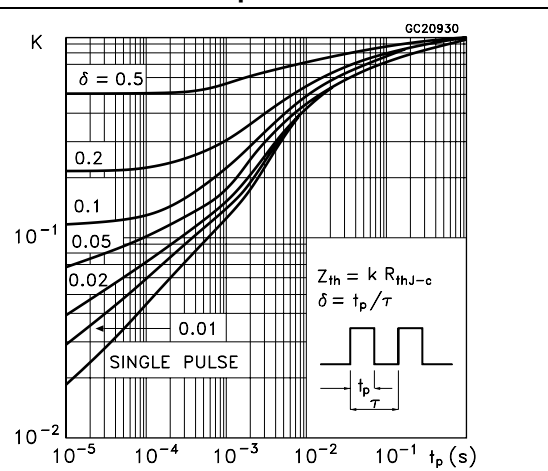


Figure 4. Safe operating area for TO-220FP

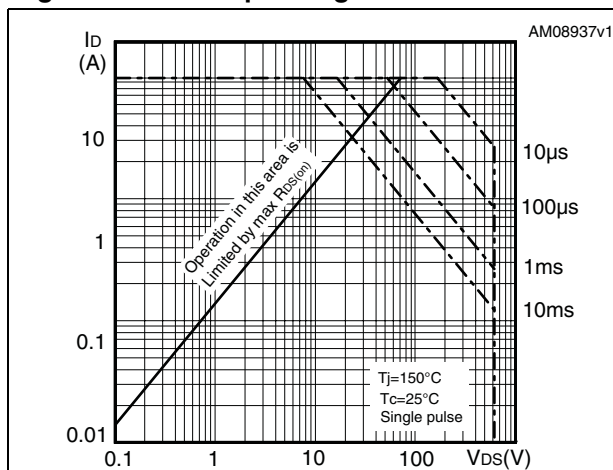


Figure 5. Thermal impedance for TO-220FP

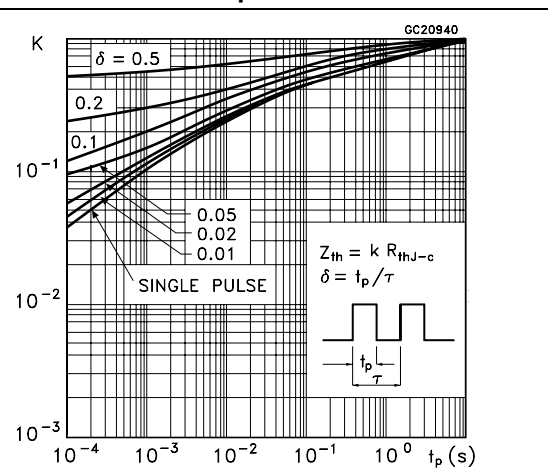


Figure 6. Safe operating area for DPAK, IPAK

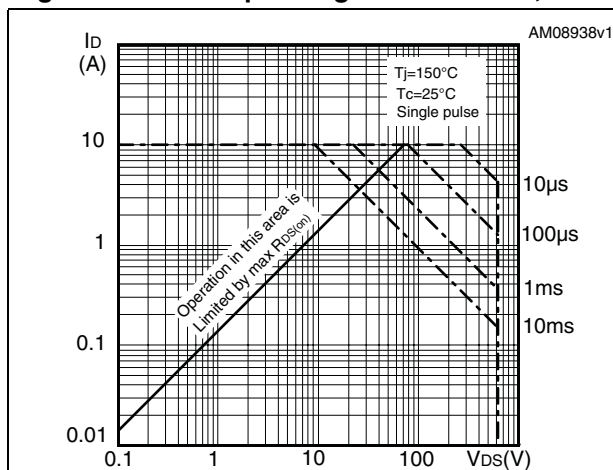


Figure 7. Thermal impedance for DPAK, IPAK

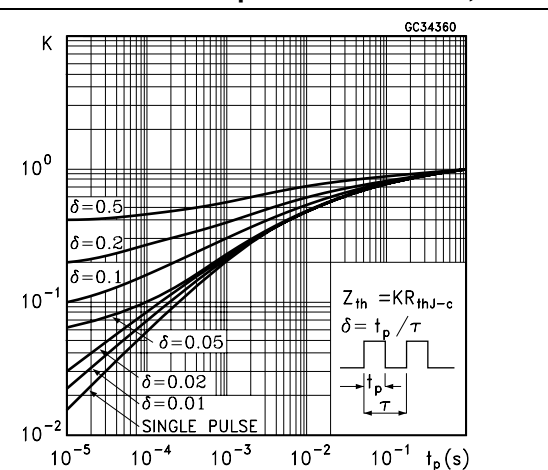


Figure 8. Output characteristics

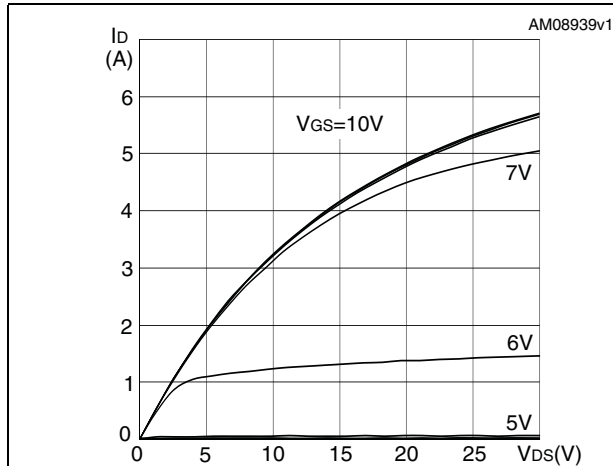


Figure 9. Transfer characteristics

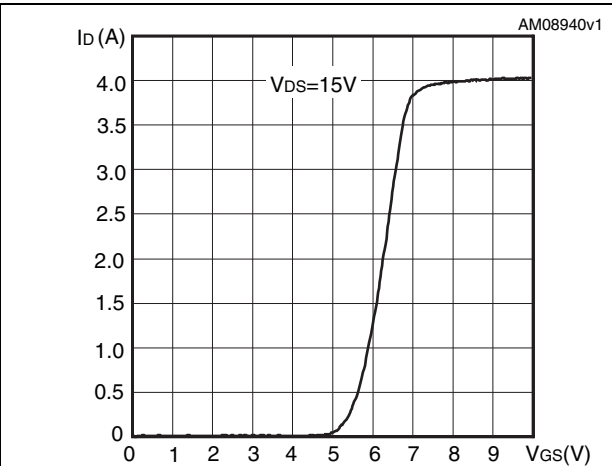


Figure 10. Gate charge vs gate-source voltage

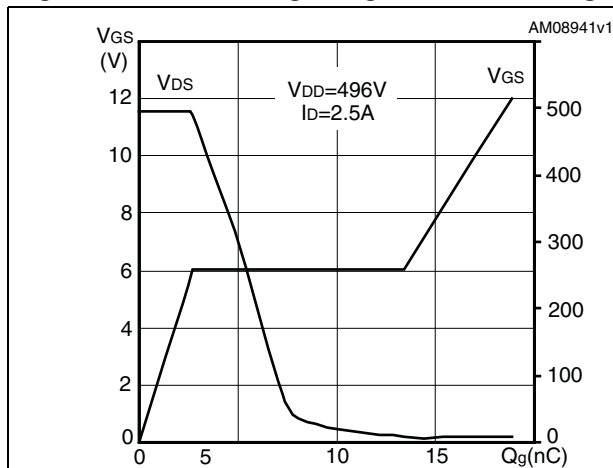


Figure 11. Static drain-source on resistance

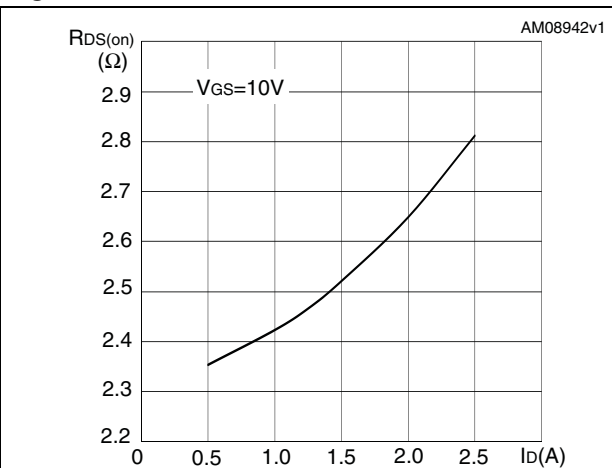


Figure 12. Capacitance variations

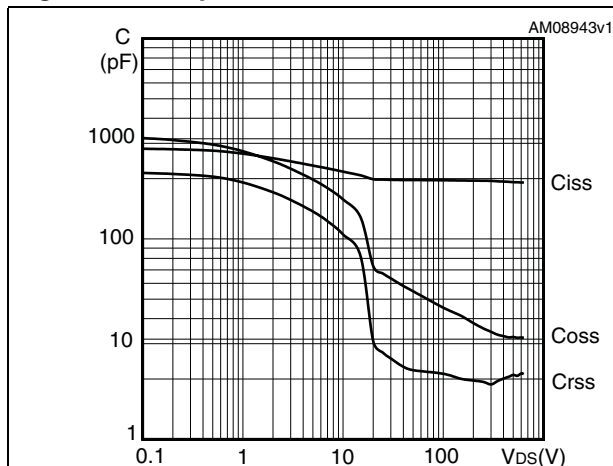


Figure 13. Output capacitance stored energy

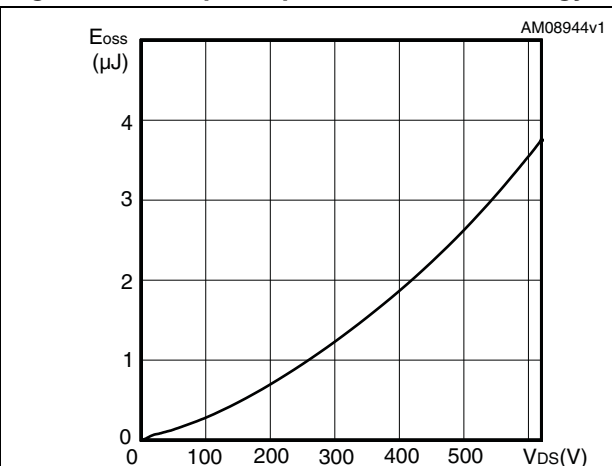
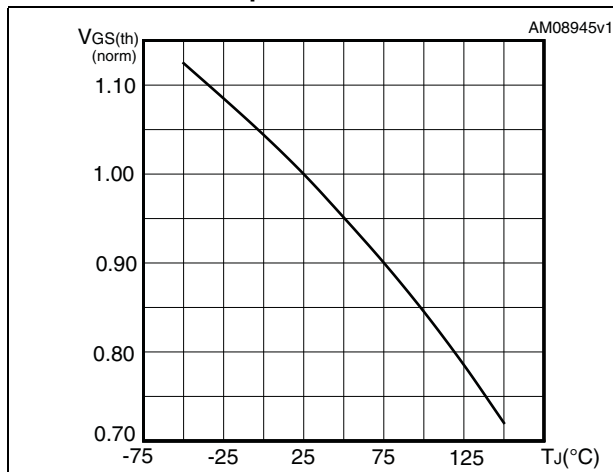
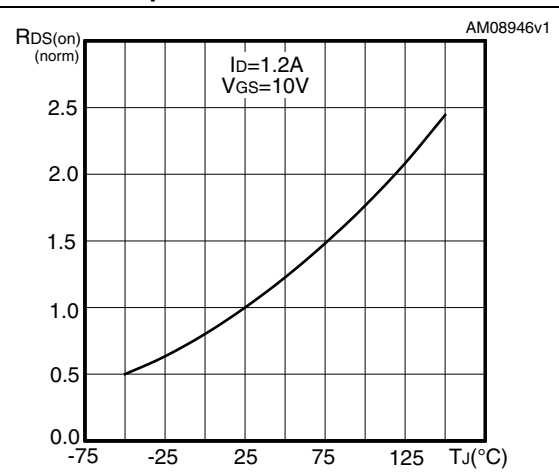
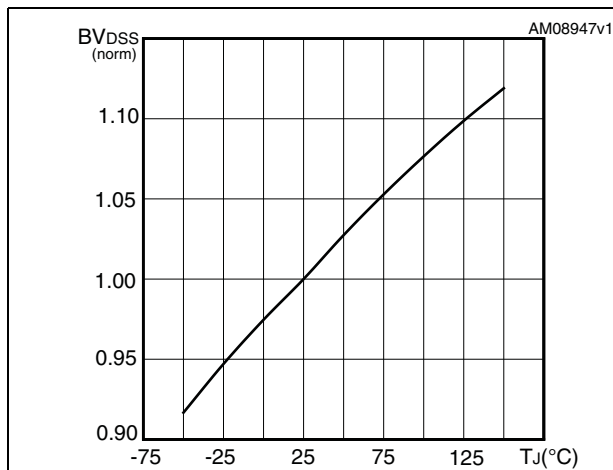
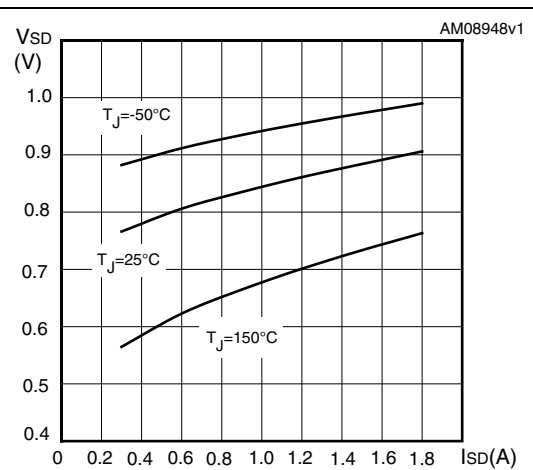
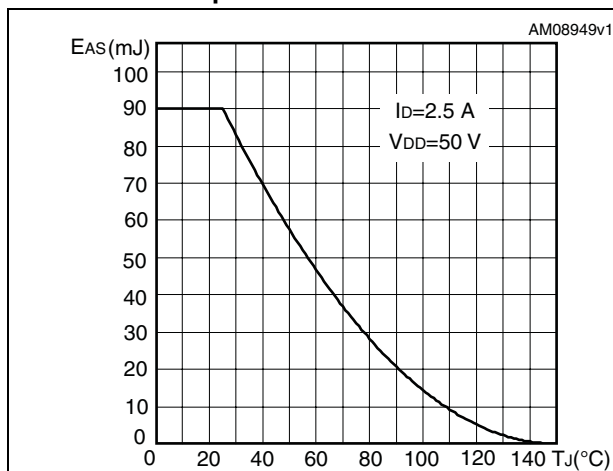


Figure 14. Normalized gate threshold voltage vs temperature**Figure 15. Normalized on resistance vs temperature****Figure 16. Normalized BV_{DSS} vs temperature****Figure 17. Source-drain diode forward characteristics****Figure 18. Maximum avalanche energy vs temperature**

3 Test circuits

Figure 19. Switching times test circuit for resistive load

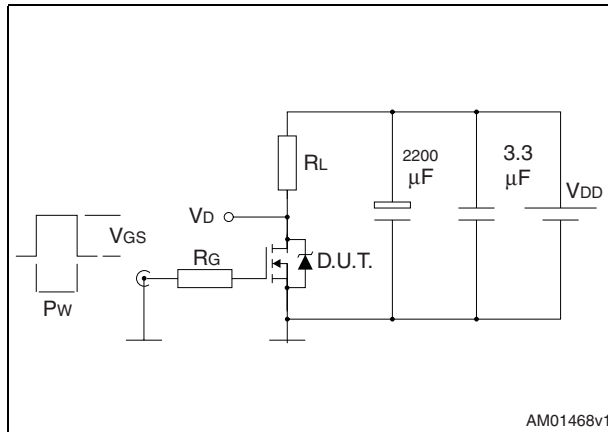


Figure 20. Gate charge test circuit

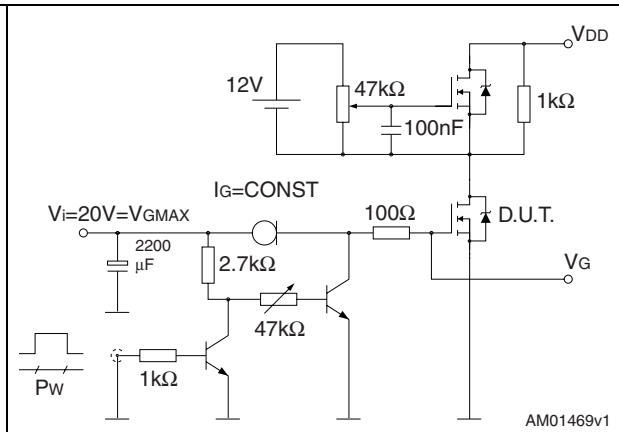


Figure 21. Test circuit for inductive load switching and diode recovery times

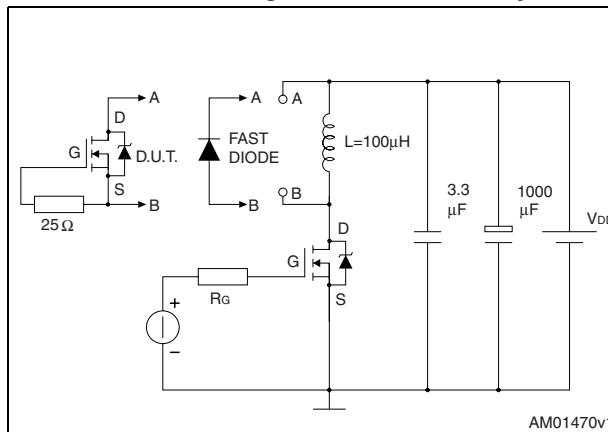


Figure 22. Unclamped Inductive load test circuit

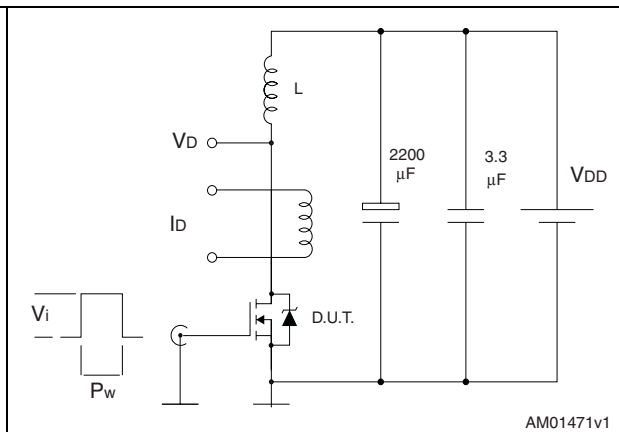


Figure 23. Unclamped inductive waveform

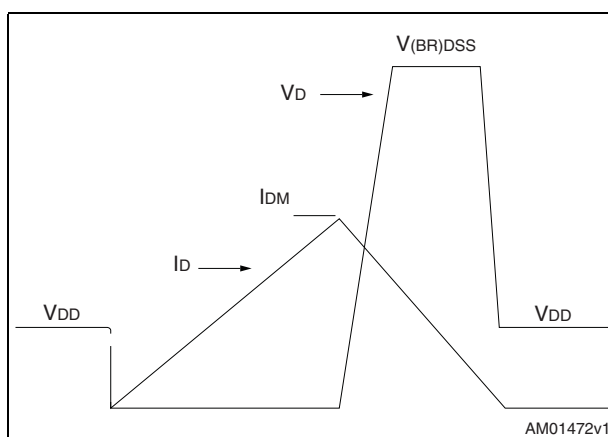
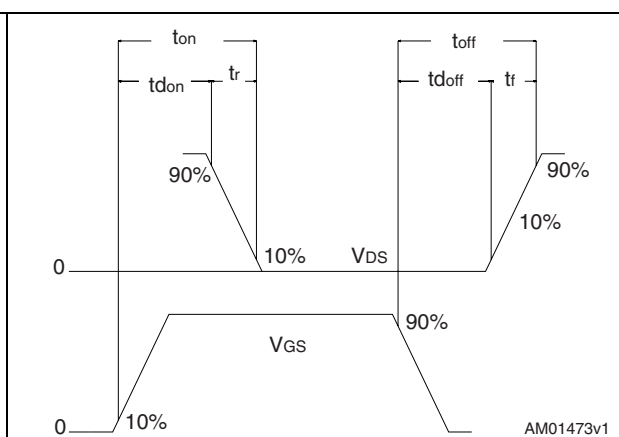


Figure 24. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 25. DPAK (TO-252) drawing

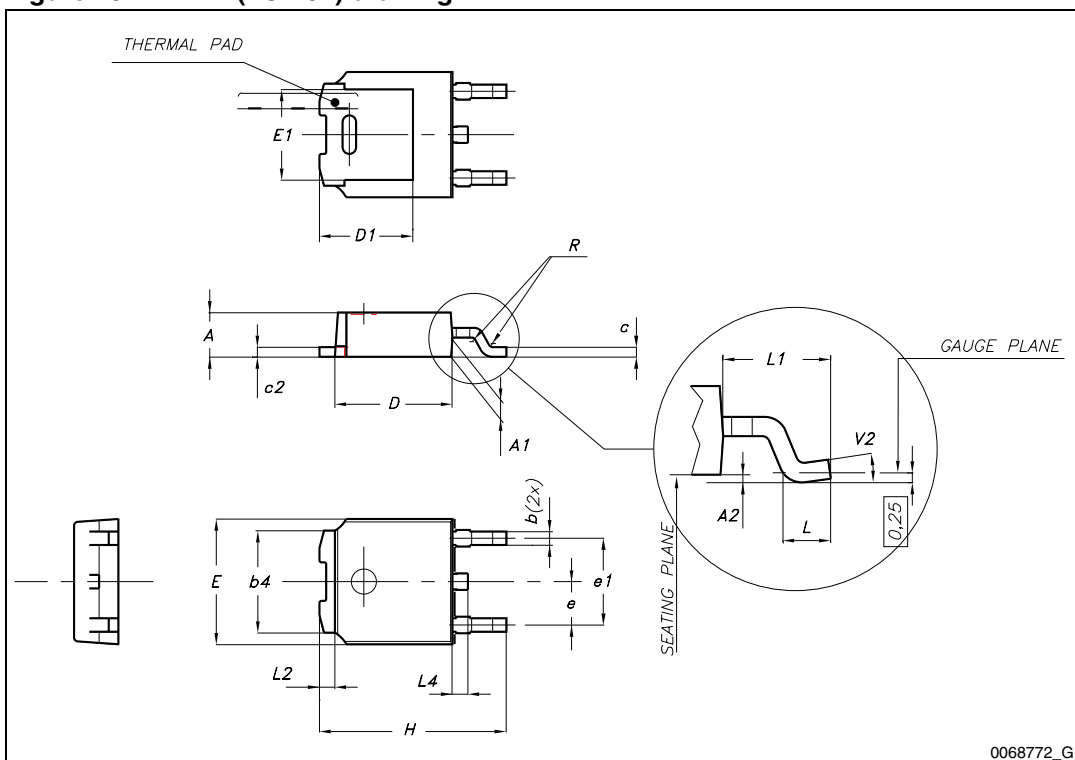


Table 11. IPAK (TO-251) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.3	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10 °	

Figure 26. IPAK (TO-251) drawing

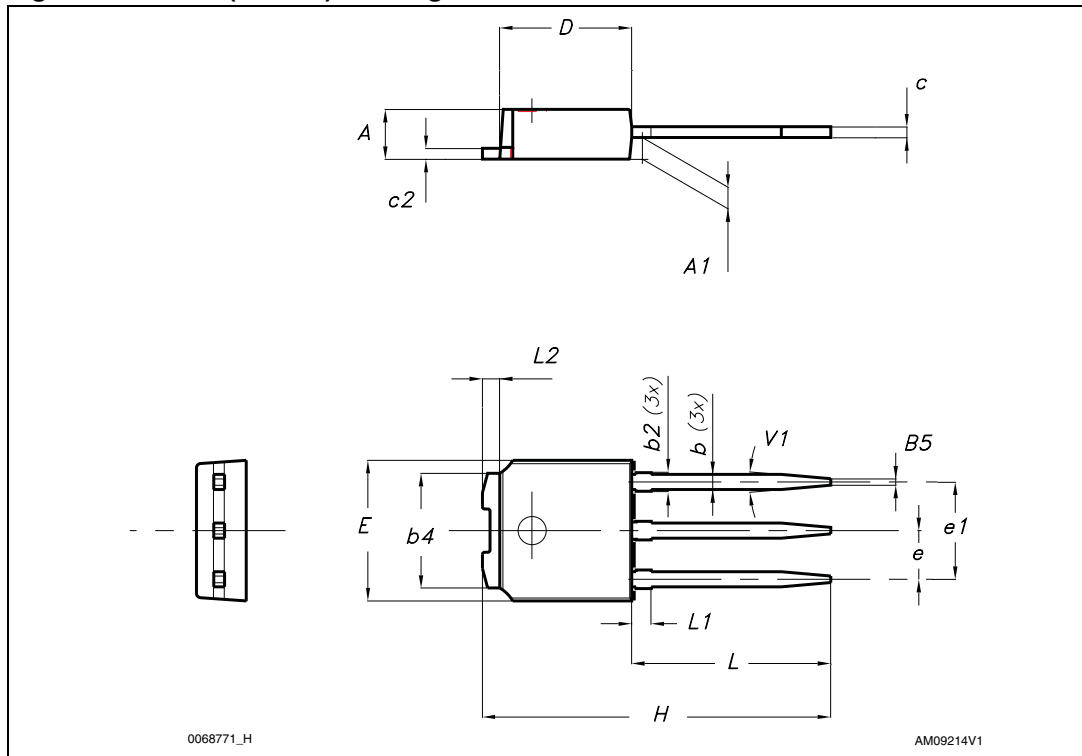


Table 12. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing

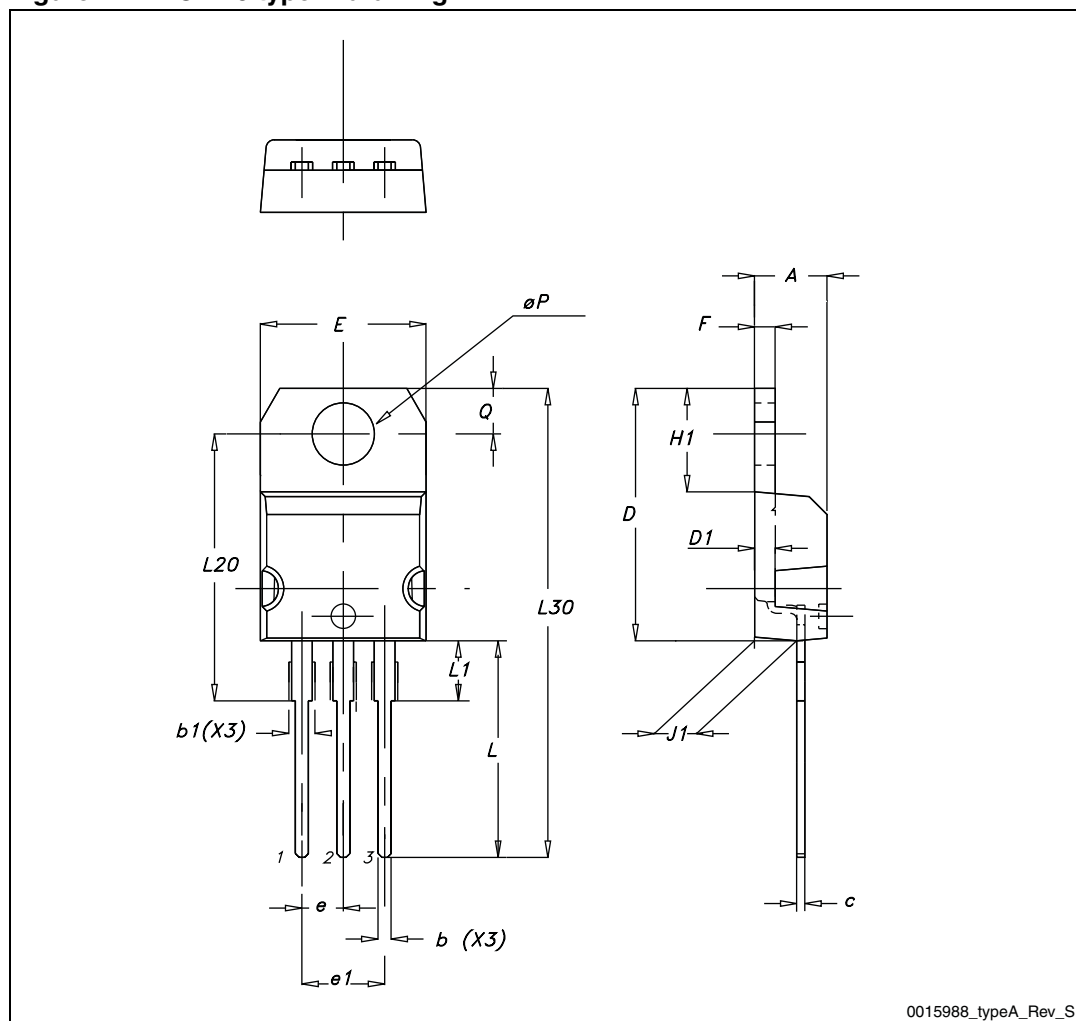
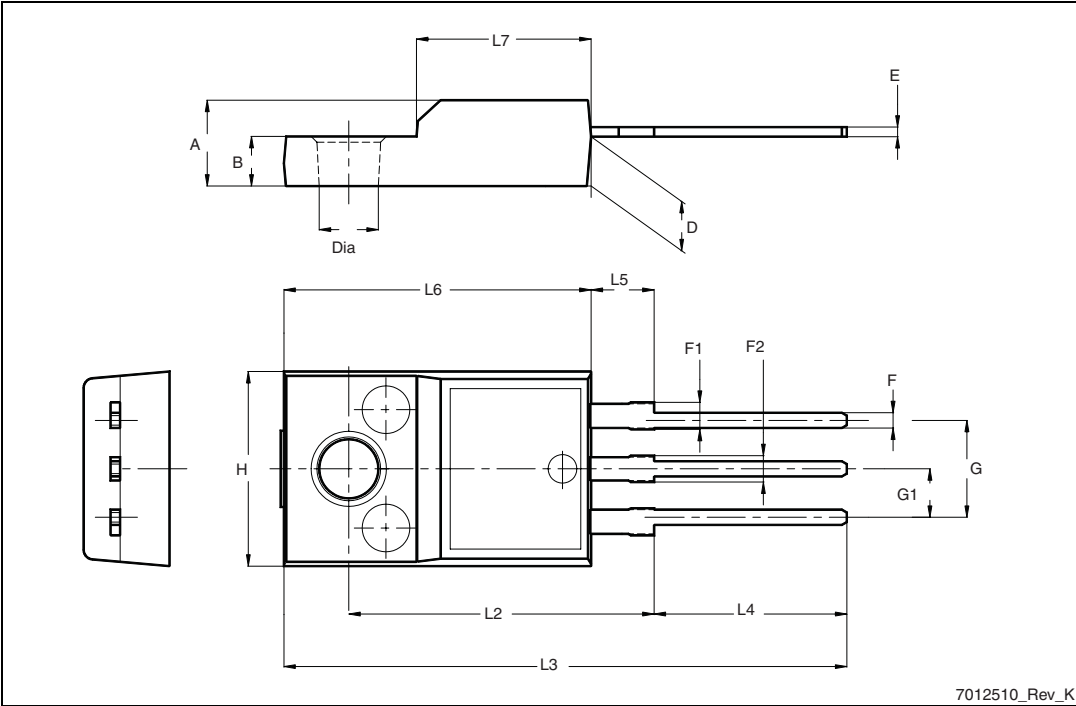


Table 13. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 28. TO-220FP drawing



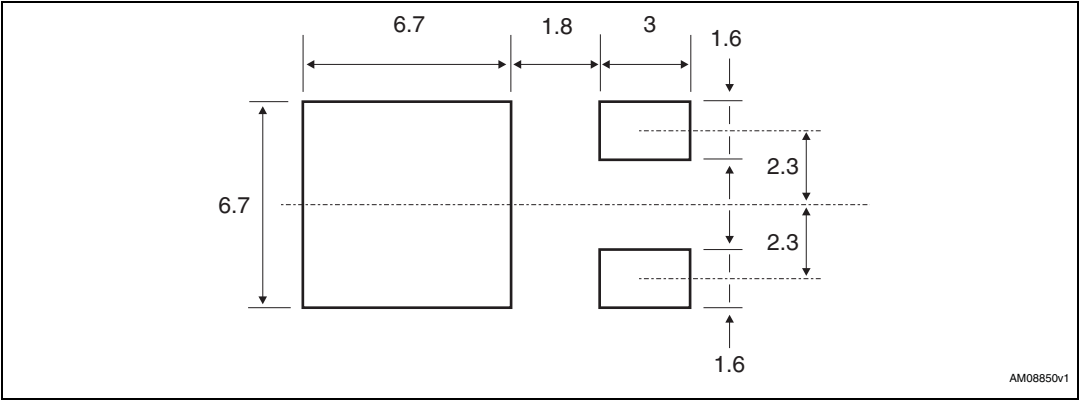
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5 Packaging mechanical data

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 29. DPAK footprint^(a)



a. All dimension are in millimeters

Figure 30. Tape for DPAK (TO-252)

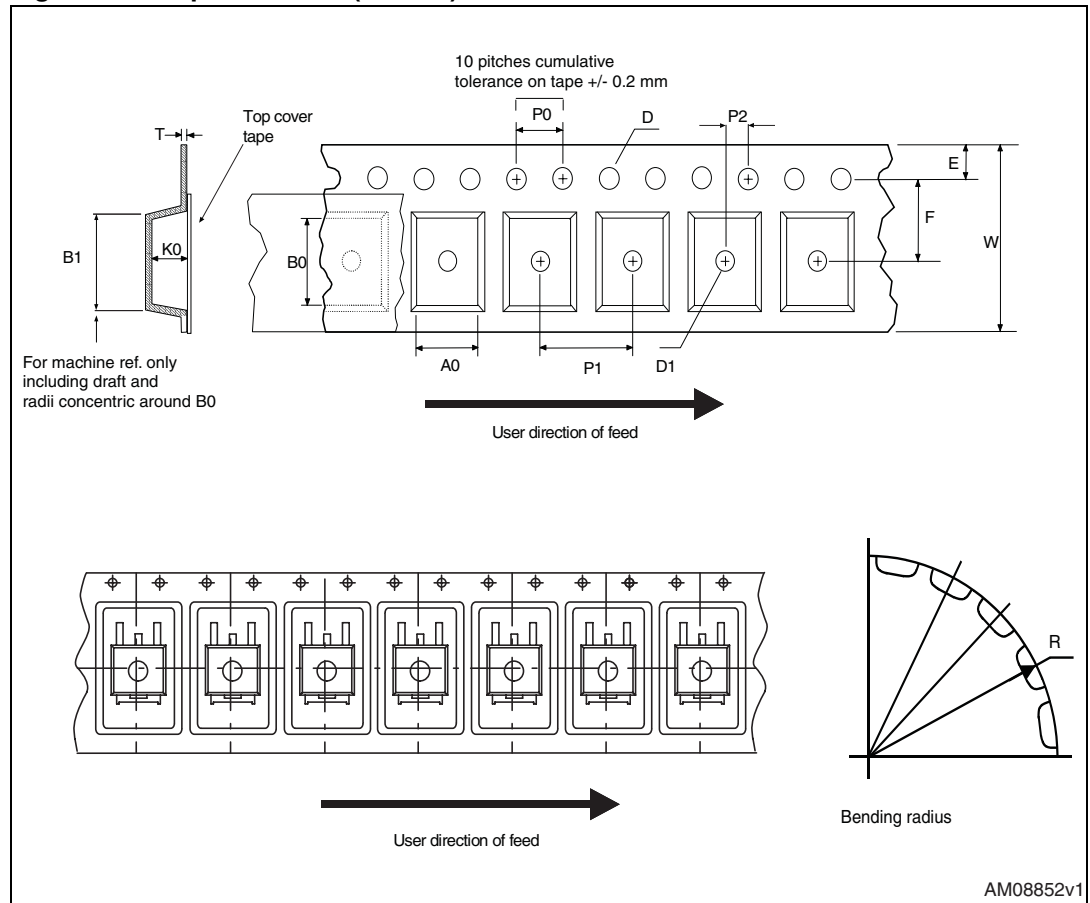
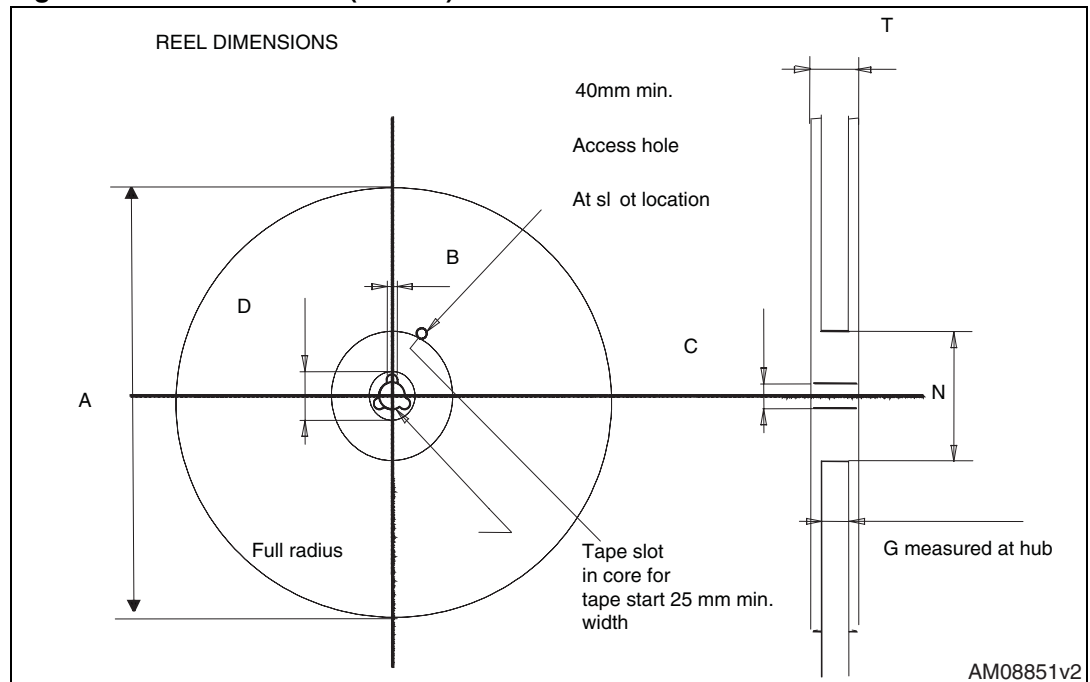


Figure 31. Reel for DPAK (TO-252)



6 Revision history

Table 15. Document revision history

Date	Revision	Changes
04-Feb-2011	1	First release.

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